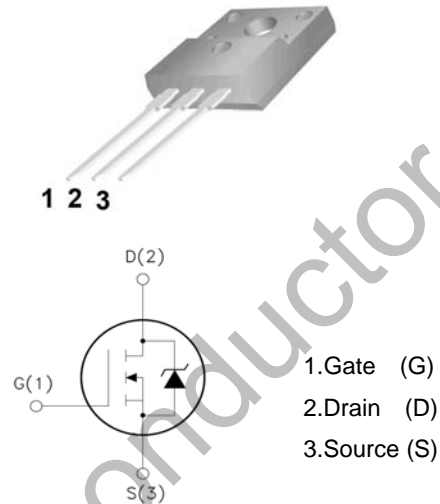




TO-220F



### Features

- Low Intrinsic Capacitances
- Excellent Switching Characteristics
- Extended Safe Operating Area
- Unrivalled Gate Charge :Qg= 8.5nC (Typ.)
- BVDSS=600V, ID=2A
- R<sub>DS(on)</sub> : 5.0Ω (Max) @VG=10V
- 100% Avalanche Tested

### Absolute Maximum Ratings (Ta=25°C unless otherwise noted)

Symbol	Parameter	WGF2N60SE	Units
V <sub>DSS</sub>	Drain-Source Voltage	600	V
I <sub>D</sub>	Drain Current	-continuous (Tc=25°C)	2*
		-continuous (Tc=100°C)	1.5*
V <sub>GS</sub>	Gate-Source Voltage	±30	V
E <sub>AS</sub>	Single Pulsed Avanche Energy	120	mJ
I <sub>AR</sub>	Avalanche Current	2	A
P <sub>D</sub>	Power Dissipation (Tc=25°C)	20	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 ~ +150	°C
TL	Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	300	°C

### Thermal Characteristics

Symbol	Parameter	Typ.	Max	Units
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	--	4.46	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	--	62.5	°C/W

\* Drain current limited by maximum junction temperature.

### Electrical Characteristics $T_c=25^\circ\text{C}$ unless other wise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\ \mu\text{A}, V_{GS}=0$	600	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D=250\ \mu\text{A}$ , Reference to $25^\circ\text{C}$	--	0.4	--	$V/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=600\text{V}, V_{GS}=0\text{V}$	--	--	1	$\mu\text{A}$
		$V_{DS}=480\text{V}, T_c=125^\circ\text{C}$			10	$\mu\text{A}$
$I_{GSSF}$	Gate-body leakage Current, Forward	$V_{GS}=+30\text{V}, V_{DS}=0\text{V}$	--	--	100	nA
$I_{GSSR}$	Gate-body leakage Current, Reverse	$V_{GS}=-30\text{V}, V_{DS}=0\text{V}$	--	--	-100	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$I_D=250\ \mu\text{A}, V_{DS}=V_{GS}$	2	--	4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$I_D=1\text{A}, V_{GS}=10\text{V}$	--	--	5.0	$\Omega$
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=25\text{V}, V_{GS}=0,$ $f=1.0\text{MHz}$	--	270	350	pF
$C_{oss}$	Output Capacitance		--	40	50	pF
$C_{rss}$	Reverse Transfer Capacitance		--	5	7	pF
<b>Switching Characteristics</b>						
$T_d(on)$	Turn-On Delay Time	$V_{DD}=300\text{V}, I_D=2\text{A}$ $R_G=25\ \Omega$	--	10	30	nS
$T_r$	Turn-On Rise Time		--	25	60	nS
$T_d(off)$	Turn-Off Delay Time		--	20	50	nS
$T_f$	Turn-Off Fall Time		--	25	60	nS
$Q_g$	Total Gate Charge	$V_{DS}=480, V_{GS}=10\text{V},$ $I_D=2\text{A}$ (	--	90	11	nC
$Q_{gs}$	Gate-Source Charge		--	1.6	--	nC
$Q_{gd}$	Gate-Drain Charge			4.3	--	nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain-Source Diode Forward Current		--	--	2	A
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current		--	--	8	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$I_D=2\text{A}$	--	--	1.5	V
$t_{rr}$	Reverse Recovery Time	$I_S=2\text{A}, V_{GS}=0\text{V}$	--	180	--	nS
$Q_{rr}$	Reverse Recovery Charge	$di_f/dt=100\text{A}/\mu\text{s}$	--	0.72	--	$\mu\text{C}$

### Typical Characteristics

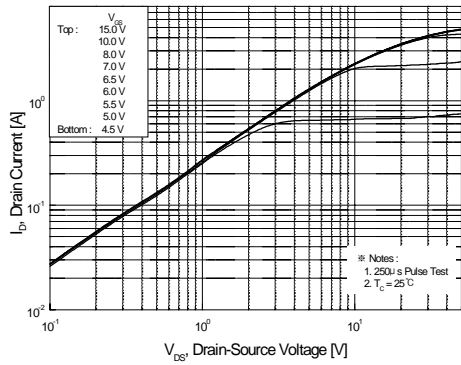


Figure 1. On-Region Characteristics

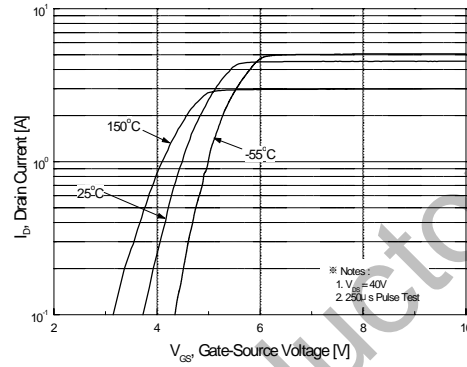


Figure 2. Transfer Characteristics

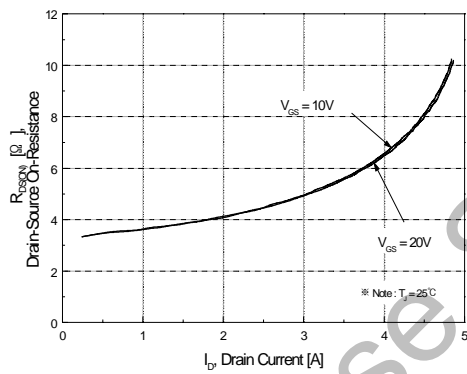


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

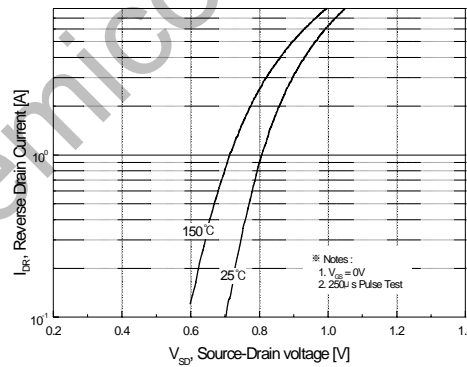


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

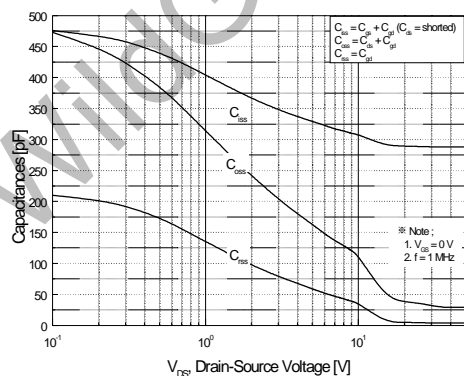


Figure 5. Capacitance Characteristics

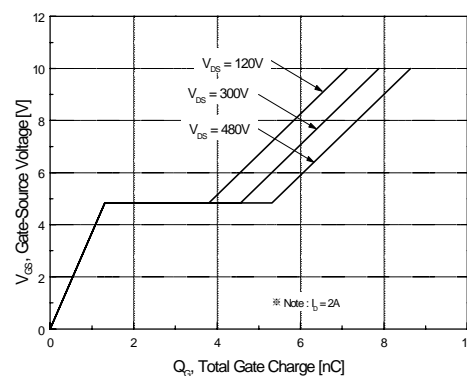


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

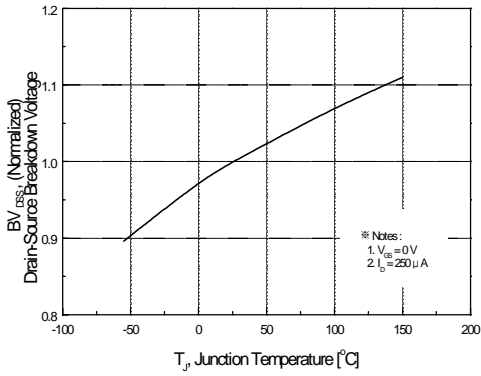


Figure 7. Breakdown Voltage Variation vs Temperature

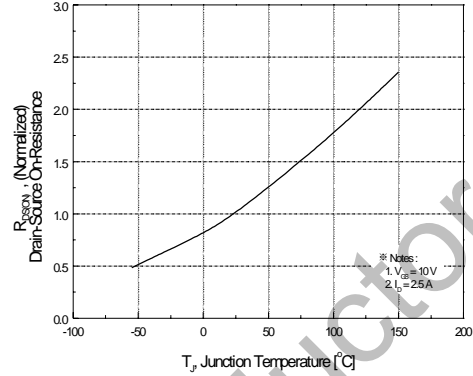


Figure 8. On-Resistance Variation vs Temperature

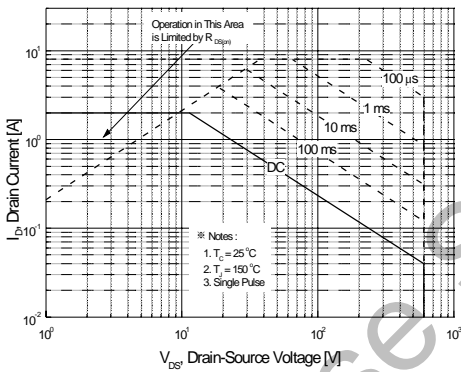


Figure 9-2. Maximum Safe Operating Area for WGF2N60S

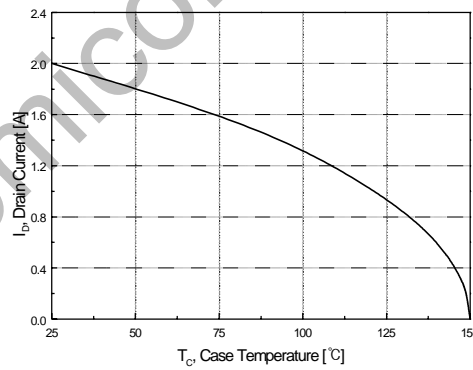


Figure 10. Maximum Drain Current vs Case Temperature

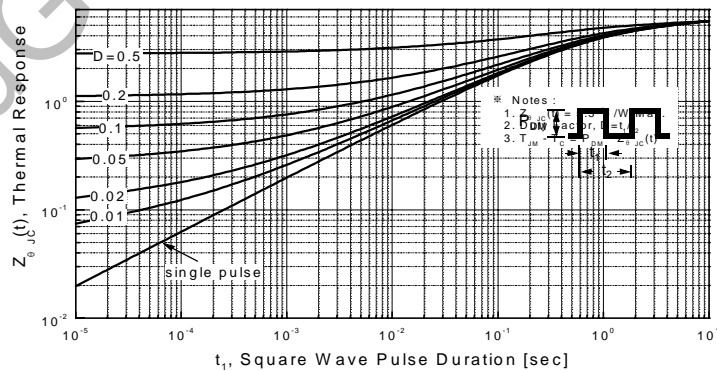
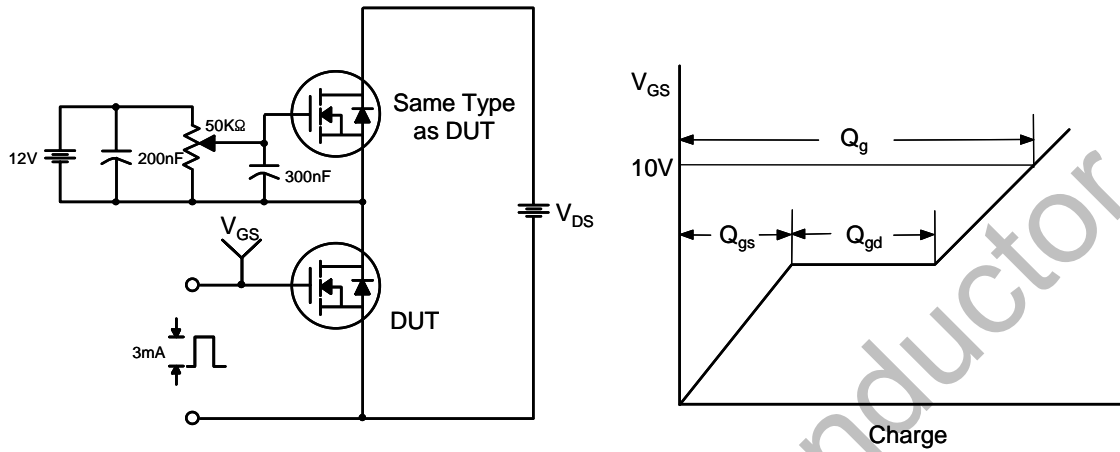
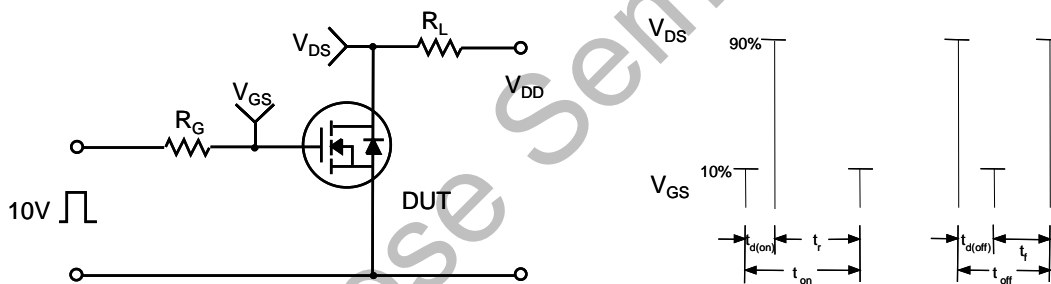


Figure 11-2. Transient Thermal Response Curve for WGF2N60S

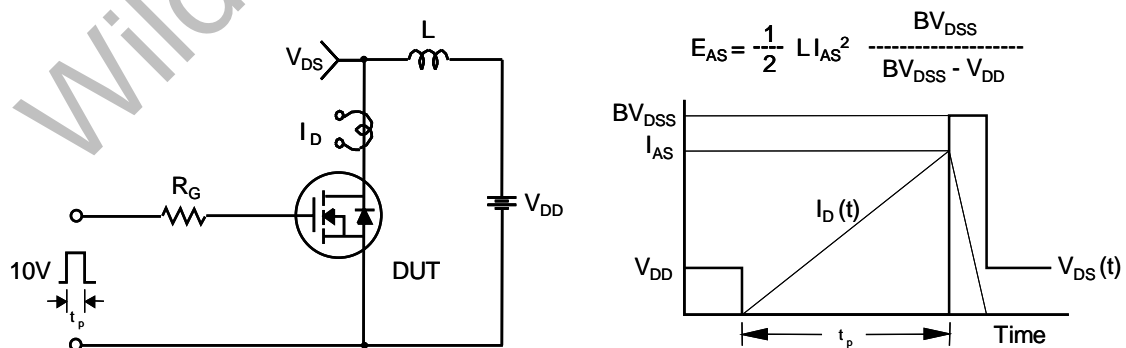
### Gate Charge Test Circuit & Waveform



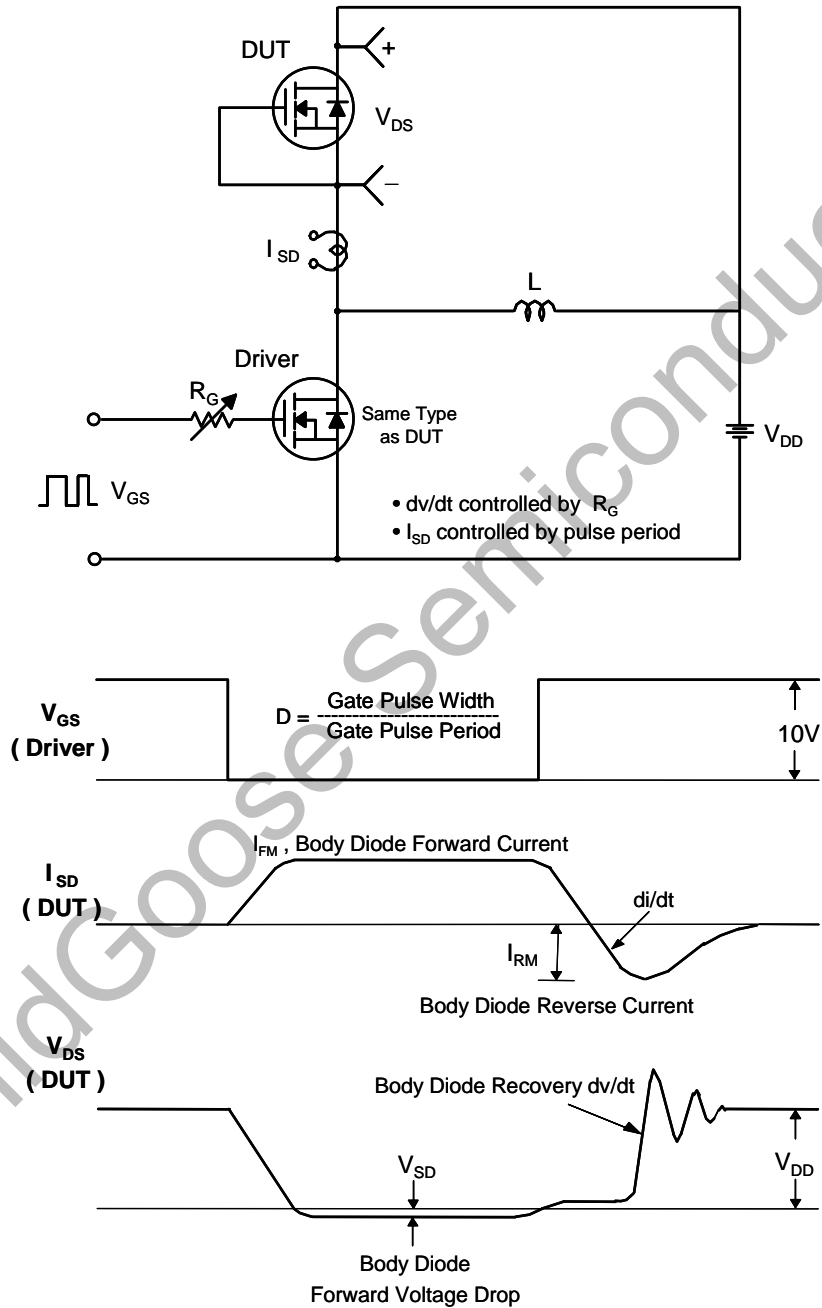
### Resistive Switching Test Circuit & Waveforms



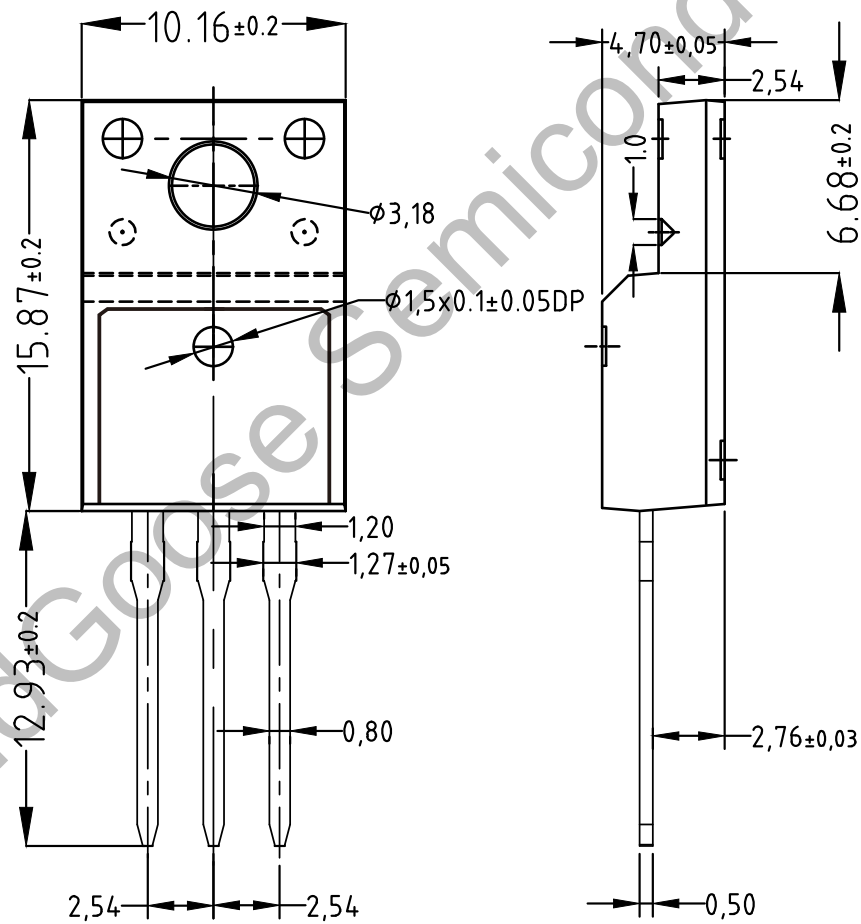
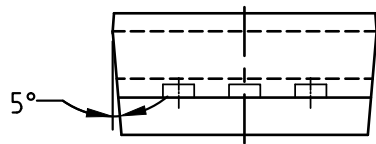
### Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms



TO-220F



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